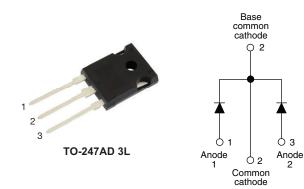
VS-C4PH6006LHN3

Vishay Semiconductors



Hyperfast Soft Recovery Diode, 2 x 30 A FRED Pt[®] Gen 4



PRODUCT SUMMARY						
Package	TO-247AD 3L					
I _{F(AV)}	2 x 30 A					
V _R	600 V					
V _F at I _F	1.37 V					
t _{rr} typ.	see Recovery table					
T _J max.	175 °C					
Diode variation	Common cathode					

FEATURES

- Gen 4 FRED Pt[®] technology
- Low I_{RRM} and reverse recovery charge
- Very low forward voltage drop
- Polyimide passivated chip for high reliability standard
- 175 °C operating junction temperature
- AEC-Q101 qualified, meets JESD 201 class 1 FREE whisker test
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION

Gen 4 Fred Pt technology, state of the art, ultralow V_{F} , soft switching optimized for Discontinuous (Critical) Mode (DCM) and IGBT F/W diode.

The minimized conduction loss, optimized stored charge and low recovery current minimized the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS			
Cathode to anode voltage	V _R		600	V			
Average rectified forward current	I _{F(AV)}	T _C = 122 °C	30	٨			
Non-repetitive peak surge current, per leg	I _{FSM}	T_C = 25 °C, t_p = 8.3 ms, half sine wave	240	A			
Operating junction and storage temperatures	T _J , T _{Stg}		-55 to +175	°C			

ELECTRICAL SPECIFICATIONS (T_J = 25 °C unless otherwise specified)								
PARAMETER	R SYMBOL		MIN.	TYP.	MAX.	UNITS		
Breakdown voltage, blocking voltage	V_{BR} , V_{R}	I _R = 100 μA	600	-	-			
		I _F = 30 A	-	1.65	2			
		I _F = 60 A	-	1.95	-	v		
For out others	V	I _F = 30 A, T _J = 125 °C	-	1.44	-			
Forward voltage	V _F	I _F = 60 A, T _J = 125 °C	-	1.78	-			
		I _F = 30 A, T _J = 150 °C	-	1.37	1.6			
		I _F = 60 A, T _J = 150 °C	-	1.68	-			
Reverse leakage current	I _R	$V_{R} = V_{R}$ rated	-	-	50			
		$T_J = 125 \ ^{\circ}C, V_R = V_R \text{ rated}$	-	-	500	μA		
Junction capacitance	C _T	V _R = 600 V	-	18.3	-	pF		



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DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25$ °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST C	MIN.	TYP.	MAX.	UNITS	
Reverse recovery time	+	$T_J = 25 \ ^{\circ}C$		-	55	-	ns
	t _{rr}	T _J = 125 °C	I _F = 30 A dI _F /dt = 1000 A/μs V _R = 400 V	-	75	-	
Peak recovery current		T _J = 25 °C		-	13	-	A
Feak recovery current	I _{RRM}	T _J = 125 °C		-	23	-	
Poverse receivery charge	0	T _J = 25 °C	V _R = 400 V	-	500	-	nC
Reverse recovery charge	Q _{rr}	T _J = 125 °C		-	1250	-	

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER SYMBOL TEST CONDITIONS		TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Thermal resistance, junction to case	R _{thJC}		-	-	1	°C/W	
Thermal resistance, case to heat sink	R _{thCS}	Mounting surface, flat, smooth, and greased	-	0.4	-		
Weight			-	6.0	-	g	
Weight			-	0.21	-	oz.	
Mounting torgue			6.0		12	kgf · cm	
Mounting torque			(5)	-	(20)	(lbf \cdot in)	
Marking device		Case style TO-247AD 3L	C4PH6006LH				

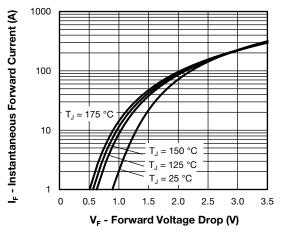
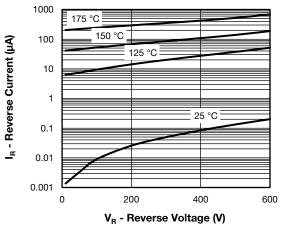


Fig. 1 - Typical Forward Voltage Drop Characteristics





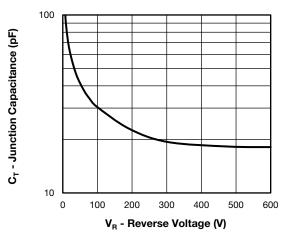
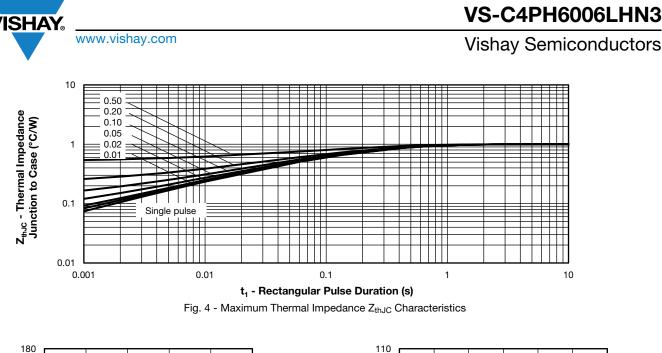
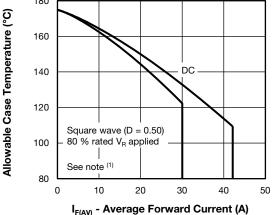
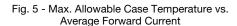


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

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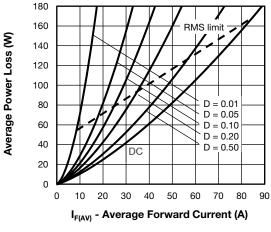
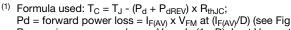


Fig. 6 - Forward Power Loss Characteristics

Note



 $\begin{array}{l} \mathsf{Pd} = \mathsf{forward} \ \mathsf{power} \ \mathsf{loss} = \mathsf{I}_{\mathsf{F}(\mathsf{AV})} \times \mathsf{V}_{\mathsf{FM}} \ \mathsf{at} \ (\mathsf{I}_{\mathsf{F}(\mathsf{AV})}/\mathsf{D}) \ (\mathsf{see} \ \mathsf{Fig. 5}) \\ \mathsf{P}_{\mathsf{d}\mathsf{R}\mathsf{EV}} = \mathsf{inverse} \ \mathsf{power} \ \mathsf{loss} = \mathsf{V}_{\mathsf{R}1} \times \mathsf{I}_{\mathsf{R}} \ (1 - \mathsf{D}); \ \mathsf{I}_{\mathsf{R}} \ \mathsf{at} \ \mathsf{V}_{\mathsf{R}} = \mathsf{rated} \ \mathsf{V}_{\mathsf{R}} \end{array}$

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110 100 Tj = 125 °C 90 t_{rr} (ns) 80 70 25 °C 60 50 400 700 1000 500 600 800 900 dl_F/dt (A/µs)

Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

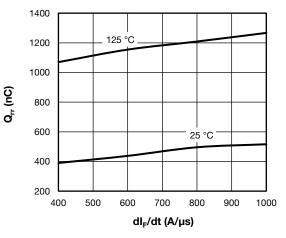


Fig. 8 - Typical Stored Charge vs. dl_F/dt

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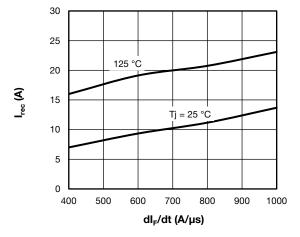


Fig. 9 - Typical Reverse Current vs. dl_F/dt

ORDERING INFORMATION TABLE

Device code	VS-	с	4	Р	н	60	06	L	Н	N3
	1	2	3	4	5	6	7	8	9	10
	1 -	- Vishay Semiconductors product								
	2 -	- Circuit configuration:								
		C =	C = common cathode							
	3 -	· FRE	FRED Gen 4							
	4 -	• P=	TO-247	' packag	e					
	5 -	- Pro	Process type:							
		H =	H = hyperfast recovery							
	6	Cur	rent rati	ng (60 =	60 A)					
	7 -	· Volt	age rati	ng (06 =	= 600 V)					
	8 -	L=	long lea	ld						
	9 -	H =	AEC-Q	101 qua	lified					
	10 -			ntal digit						
		N3 :	= haloge	en-free,	RoHS-c	ompliar	nt, and t	otally le	ad (Pb)	-free

ORDERING INFORMATION (Example)							
PREFERRED P/N QUANTITY PER TUBE MINIMUM ORDER QUANTITY PACKAGING DESCRIPTIO							
VS-C4PH6006LHN3	25	500	Antistatic plastic tube				

LINKS TO RELATED DOCUMENTS				
Dimensions	TO-247AD 3L	www.vishay.com/doc?95626		
Part marking information	TO-247AD 3L	www.vishay.com/doc?95007		

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Vishay Semiconductors

TO-247AD 3L

DIMENSIONS in millimeters and inches



View B

SYMBOL	MILLIN	IETERS	INCHES		NOTES
STIVIBOL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.65	5.31	0.183	0.209	
A1	2.21	2.59	0.087	0.102	
A2	1.50	2.49	0.059	0.098	
b	0.99	1.40	0.039	0.055	
b1	0.99	1.35	0.039	0.053	
b2	1.65	2.39	0.065	0.094	
b3	1.65	2.34	0.065	0.092	
b4	2.59	3.43	0.102	0.135	
b5	2.59	3.38	0.102	0.133	
с	0.38	0.89	0.015	0.035	
c1	0.38	0.84	0.015	0.033	
D	19.71	20.70	0.776	0.815	3
D1	13.08	-	0.515	-	4

(2, 52, 51) (4) Section C - C, D - D, E - E

SYMBOL	MILLIN	IETERS	INC	HES	NOTES		
STNIBOL	MIN.	MAX.	MIN.	MAX.	NOTES		
D2	0.51	1.30	0.020	0.051			
E	15.29	15.87	0.602	0.625	3		
E1	13.46	-	0.53	-			
е	5.46	5.46 BSC		5 BSC			
ØК	0.2	0.254		0.254 0.010		010	
L	19.81	20.32	0.780	0.800			
L1	3.71	4.29	0.146	0.169			
ØР	3.56	3.66	0.14	0.144			
Ø P1	-	6.98	-	0.275			
Q	5.31	5.69	0.209	0.224			
R	4.52	5.49	0.178	0.216			
S	5.51 BSC		0.217	' BSC			

Notes

⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5M-1994

(2) Contour of slot optional

- ⁽³⁾ Dimension D and E do not include mold flash. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- ⁽⁵⁾ Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- ⁽⁷⁾ Outline conforms to JEDEC[®] outline TO-247 with exception of dimension A min., D, E min., Q min., S, and note 4

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